

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A silicon carbide product comprising single-crystalline silicon carbide or chemical vapor deposited polycrystalline silicon carbide ~~that is obtained by a CVD method~~, wherein the single-crystalline silicon carbide or chemical vapor deposited polycrystalline silicon carbide are free from sintering agent ~~is cleaned only by an acidic solution, the single-crystalline silicon carbide or polycrystalline silicon carbide having and have~~ a surface with a concentration of metal impurities equal to or less than 1×10^{11} atoms/cm².

2. (Currently Amended) The silicon carbide product according to claim 1, wherein said metal impurities are at least one of iron or an iron compound, Ni, and Cu and wherein each of iron or iron compound, Ni and Cu has a concentration of less than 1×10^{10} atoms/cm².

3. (Previously Presented) The silicon carbide product according to claim 1 or 2, wherein said product is at least one of a semiconductor device, a semiconductor device manufacturing member, and a structure.

4. (Currently Amended) A silicon carbide product cleaning method comprising immersing single-crystalline silicon carbide or chemical vapor deposited polycrystalline silicon carbide free from any sintering agent ~~that is obtained by a CVD method~~ in an acid, wherein the step of immersing the single-crystalline silicon carbide or the chemical vapor deposited polycrystalline silicon carbide in the acidic solution reduces surface [[metal]] iron or iron compound, Ni or Cu impurities of the single-crystalline silicon carbide or the chemical vapor deposited polycrystalline silicon carbide ~~to 1×10^{11} atoms/cm² or less~~ such that each of the iron or iron compound, Ni and Cu impurities has a concentration of less than 1×10^{10} atoms/cm².

5. (Currently Amended) A method of manufacturing a silicon carbide product composed of single-crystalline silicon carbide or chemical vapor deposited polycrystalline silicon carbide ~~that is obtained by a CVD method~~, comprising:

forming the single-crystalline silicon carbide or the chemical vapor deposited polycrystalline silicon carbide; and

cleaning the single-crystalline silicon carbide or the chemical vapor deposited polycrystalline silicon carbide only by an acidic solution to reduce surface ~~[[metal]]~~ iron or iron compound, Ni or Cu impurities to 1×10^{11} atoms/cm² or less such that each of the iron or iron compound, Ni and Cu impurities has a concentration of less than 1×10^{10} atoms/cm².

6. (Original) The method according to claim 5, wherein said acid is hydrofluoric acid or hydrochloric acid.

7. (Original) The method according to claim 6, wherein said hydrofluoric acid has a concentration exceeding 45%.

8. (Original) The method according to claim 7, wherein said hydrofluoric acid has a concentration of about 50%.

9. (Original) The method according to claim 6, wherein said hydrochloric acid has a concentration of 35% or more.

10. (Original) The method according to claim 9, wherein said hydrochloric acid has a concentration of about 36%.

11. (Original) The method according to claim 5, wherein said acid is a liquid containing sulfuric acid and a hydrogen peroxide solution.

12. (Original) The method according to claim 11, wherein said liquid containing said sulfuric acid and said hydrogen peroxide solution has a pH of 4 or less.

13. (Original) The method according to claim 12, wherein said sulfuric acid and said hydrogen peroxide solution respectively have concentrations of about 97% and about 30% and are mixed in a volume ratio of about 4:1.

14. (Currently Amended) A silicon carbide product free from sintering agent and manufactured by the method according to claim 5, said silicon carbide product being a semiconductor device, a semiconductor device manufacturing member, or a structure.

15-16. (Cancelled).